

# Novel Remapping Method for HR-EBSD based on Computer Vision Algorithm

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Total Deformation

# Crystal Deformation

deform crystal lattice

 $\mathbf{\nabla} \mathbf{F}^{e}$ 

(rotation and elastic stretch)



Deformation gradient tensor:

 $F = F^e F^p$ 

Elastic stretch: shift of the zone axis and changes in the interplanar angles

$$\varepsilon = \frac{1}{2} \left( F^e + F^{e^T} \right) - I$$

Lattice rotation: whole pattern rotation

$$\omega = \frac{1}{2} \left( F^e - F^{e^T} \right)$$

create and move dislocations

Fp

K.C. Le *et al.*, 2015; Kröner, 1958; B.C. Larson *et al*, 2007 10/31/2020

F⁄





# HR-EBSD (Cross-Correlation)

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### **Cross-Correlation**



# Higher level of sensitivity:

- Rotation:  $1x10^{-4}$  rad or 0.006 °
- Elastic strain: 1x10<sup>-4</sup>
- GND lower noise floor:
  - Hough:  $\Delta \rho \approx 10^{14} \text{ lines/m}^2$
  - HR-EBSD:  $\Delta \rho \approx 10^{12}$  lines/m<sup>2</sup>

 $f_{test} * f_{ref} = \mathfrak{I}^{-1}[\mathfrak{I}(f_{test}) \cdot conj(\mathfrak{I}(f_{ref}))]$ 10/31/2020 Wilkinson et al, 2006

Shift of the XCF peak from the origin represents the shift of the test ROI from reference ROI.

# HR-EBSD (Cross-Correlation)

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Non-linear minimization method to obtain deformation gradient tensor ( $F^e$ ):

$$minf(F^{e}) = \sum_{\{ROI\}} \frac{1}{2} \left| \frac{Z^{*}}{(F^{e} \cdot \vec{r}) \cdot \vec{k}} F^{e} \cdot \vec{r} - (\vec{r} + \vec{q}) \right|^{2} \stackrel{\vec{r}: \text{ center of ROI}}{Z^{*}: \text{ detector distance}} \\ \vec{q}: \text{ measured shift}$$

 $F^e$  between two images can be calculated from shifts measured between many regions of interest (ROIs).

**Reference Pattern** 



<sup>10/31/2020</sup> Maurice *et al.*, 2012









# Cross-Correlation: Limitation

0.01

0.009

0.008

0.007

0.006 Error

Rotation 0.005

0.003

0.002

0.001

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# Cross-Correlation Between Patterns of Large Relative Rotations



### **Rotation and Strain Error**

0.15



#### **Reference Pattern**

0.1

Applied rotation  $\phi_1$  ( $\omega_{12}$ ) in rad

0.05

 $-\omega_{31}$  -



#### Test Pattern



#### **Total Shift**



XCF peak changes at higher rotations

Multiple peaks

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• Peak shape distortion

# Pattern Remapping Technique

Total deformation gradient tensor

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 $F_f = F_i \cdot R_f$ 



Remapping using orientation matrix (Maurice *et al*, 2012)

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- Remapping using cross-correlation (Britton *et al*, 2012)
- 3. Global matching using computer vision for remapping (Zhu et al, 2019)

Britton *et al*, Ultramicroscopy 2012 Maurice *et al.*, Ultramicroscopy 2012 Zhu et al, Ultramicroscopy 2020







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# Cross-Correlation (after Remapping)

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### Cross-Correlation (No remapping)



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 $F_f = F_i \cdot R_f$ 

### Cross-Correlation (After remapping)







• No peak distortion for the cross-correlation after remapping

0.6

0.4

0.2

• Single high intensity peak only

### **GPU Acceleration for Image Registration Materials Research Center**



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### Angular Resolution of Different Methods

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Reference pattern: [0,0,0,] Test pattern: [i,0,0] i=0°~10°

(a) cross-correlation



- (b) image registration
- (c) 1<sup>st</sup> pass cross-correlation for remapping + 2<sup>nd</sup> pass cross-correlation for infinitesimal deformation
- (d) 1<sup>st</sup> pass image registration for remapping + 2<sup>nd</sup> pass cross-correlation for infinitesimal deformation
- image registration (b) can not be used alone for accuracy.
- Method (d) outperforms (a) and (b).
- (d) slightly improves angular resolution compared to (c).

# Phantom strain and stress

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#### Unregistered



#### Registered



#### **Unregistered Residual**



#### **Registered Residual**



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# Zoom and Shift Correction



Zoom or Shrinkage Correction: ratio between detector distance (DD) between the reference and test patterns.

Shift Correction: difference in beam position on the sample.

Britton *et al*, Ultramicroscopy 2011

Test Sample: Single crystal Silicon (200 µm by 200 µm)





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### Additively Manufactured Inconel 625

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25 µm

Reference Misorientation



EBSP



**Band Contrast** 



Reference points obtained based on: band contrast mean angular deviation

# Lattice Rotation, Strain, Stress

### $\omega_{12}$ $\omega_{31}$ $\omega_{23}$ 0.04 0.02 0 -0.02 -0.04 $\epsilon_{12}$ $\epsilon_{11}$ e22 ×10<sup>-</sup> $\sigma_{12}$ $\sigma_{11}$ $\sigma_{22}$

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- Columnar growth in the large grain (sub-grain structure)
- Large compressive or tensile residual stresses in the columnar grain.
- Stress concentration near triple junctions and high angle grain boundaries (strain compatibility).

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### Hough vs HR-EBSD based GND Density



- High density dislocation structures are very similar between the two
- Low density dislocation structures are more clearly revealed in HR-EBSD based GND map

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# Summary

- Multiresolution image registration is a fast and accurate remapping for HR-EBSD.
- Phantom strain <  $2 \times 10^{-4}$  and phantom stress < 30 MPa.
- Lower GND noise floor ( $\Delta \rho \approx 2 \ge 10^{12} \text{ lines/m}^2$ )
- Additively manufactured Inconel 625 shows significant residual stress build-up in the columnar grain region/ stress concentration near grain boundaries and triple junctions (strain compatibility).

<u>Zhu, C</u>., Kaufmann, K. and Vecchio, K., 2020. Novel Remapping Approach for HR-EBSD based on Demons Registration, Ultramicroscopy

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# HR-EBSD (Essentials)



Deformation gradient tensor F between two images can be calculated from shifts measured between many regions of interest (ROIs). Non-linear minimization method to obtain deformation gradient tensor:

$$minf(F) = \sum_{\{ROI\}} \frac{1}{2} \left| \frac{Z^*}{(F \cdot \vec{r}) \cdot \vec{k}} F \cdot \vec{r} - (\vec{r} + \vec{q}) \right|^2 \text{ (Levenberg-Marquardt)}$$
$$*F_{\text{sample}} = R_{\theta_{tilt}} F R_{\theta_{tilt}}^T \text{ (Coordinate Transformation)}$$
$$F_{sample} = PDQ^T \text{ (SVD)}$$
$$R_{sample} = PQ^T \text{ (Rotation Matrix)}$$

 $\omega$  can then be obtained through parametrizing  $R_{sample}$  using Rodrigues vector i.e. axis-angle pair ( $m_k$ ,  $\theta$ )

$$\omega_{ij} = -\varepsilon_{ijk} m_k \theta = -\varepsilon_{ijk} \theta_k \qquad (Lattice Rotation Tensor)$$

$$\varepsilon_{sample} \approx \frac{1}{2} \left( F_{sample} + F_{sample}^{T} \right) - I$$

(Residual Strain Tensor)

 $\sigma_{sample} = C : \varepsilon_{sample} (t = \sigma_{sample} Z_s = [0,0,0])$  (Residual Stress Tensor)

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\*Coordinate transformation is required to bring it from detector frame  $(X_d, Y_d, Z_d)$  to sample frame  $(X_s, Y_s, Z_s)$ 

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### Higher level of sensitivity:

- Rotation: whole diffraction pattern moving (1x10<sup>-4</sup> rad)
- Elastic stretch: change interplanar angles and lattice spacing (1x10<sup>-4</sup>)
- GND lower limit:
  - $\Delta \theta = 0.5^{\circ}$  (Hough based)  $\rightarrow \Delta \rho \approx 2 \times 10^{14} \text{ lines/m}^2$
  - $\Delta \theta = 10^{-4} \text{ rads}$  (XCF based)  $\rightarrow \Delta \rho \approx 2 \text{ x } 10^{12} \text{ lines/m}^2$

### Obtaining the total shift vectors

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# Hough vs HR-EBSD based Lattice Rotation

Lattice Rotation (rad) 0 700-

-0.04

0

50

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Distance (µm)

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HR-EBSD  $\omega_{31}$ 





HR-EBSD

Hough-EBSD

150

100

Distance (µm)

HR-EBSD  $\omega_{23}$ 

Hough-EBSD lattice rotation tensor

$$\omega_{23} \approx \frac{1}{2}(g_{23} - g_{32})$$
$$\omega_{31} \approx \frac{1}{2}(g_{31} - g_{13})$$
$$\omega_{12} \approx \frac{1}{2}(g_{12} - g_{21})$$

- Nominally similar values and trend, especially  $\omega_{23}$
- Hough based lattice rotation tensor can be used as a quick check



# Hough Indexing

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